

TERMINATION STRUCTURE FOR MOSGATED POWER DEVICES

ABSTRACT OF THE DISCLOSURE

The termination of a MOSgated device is formed by a trench bevel which surrounds the active device area. The trench bevel has flat walls which extend into and through the epitaxial layer containing the active area which has a lateral extend equal to or less than the thickness of the epitaxial layer. The surface of the bevel is coated with a resistive film, preferably, an amorphous silicon which connects the device source to the device drain to cause the electric field in the epitaxial silicon to be linearly distributed over the length of the bevel.